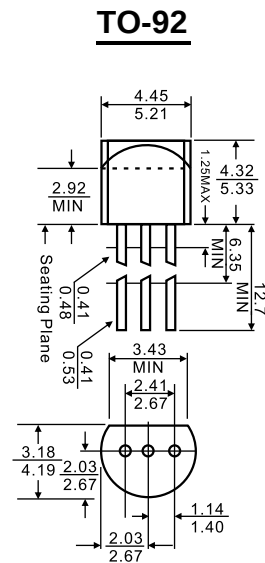




1. EMITTER
2. BASE
3. COLLECTOR

Features

- ✧ **Switching and amplification in high voltage**
- ✧ **Applications such as telephony**
- ✧ **Low current(max. 600mA)**
- ✧ **High voltage(max.160v)**



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.625	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -1mA$	80			
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -10mA$	60		240	
	$h_{FE(3)}$	$V_{CE} = -5V, I_C = -50mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 30MHz$	100		300	MHz

Typical Characteristics

